

**PECULIARITIES OF CONDUCTIVITY DOSE DEPENDENCES OF THE
PREVIOUSLY IRRADIATED SEMICONDUCTORS ON AN EXAMPLE OF INDIUM
ANTIMONIDE, IRRADIATED WITH PROTONS**

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First results of investigation of defects formation efficiency in the previously irradiated semiconductors on an example of 47 MeV protons irradiated indium antimonide is given. The conclusion is made, that combination of preliminary irradiation with annealing is expected to become the basis of thermal-radiation technology of semiconductors radiation hardness increasing.